



Thematic Network on Silicon on Insulator Technology, Devices and Circuits.
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EUROSIO "Who is Who" Guide

Name of the organisation

<i>Organization Legal name:</i>	Centre National de la Recherche Scientifique (AD13), 3 rue Michel Ange, 75794 Paris cedex 16.
<i>Organization short name:</i>	UM2/GES/JRU5650
<i>Internet homepage:</i>	

Contact person

<i>Name:</i>	CAMASSEL	<i>Title:</i>	<i>Prof.</i>
<i>First name:</i>	JEAN	<i>Sex:</i>	<i>M</i>
<i>Phone:</i>	(33)(0)4 67 14 39 73	<i>E-mail:</i>	jean.camassel@ges.univ-montp2.fr
<i>Postal Address</i>	Groupe d'Etude des Semiconducteurs (G.E.S.) - CC 074, Université Montpellier, place Eugène Bataillon, 34095 Montpellier cedex5		

Other Senior Researchers: (up to 10 names, please include e-mail address)

Sylvie CONTRERAS (sylvie.contreras@ges.univ-montp2.fr)
Antoine TIBERJ (antoine.tiberj@ges.univ-montp2.fr)

Experience and expertise fields: (50 words)

The group at UM2 has more than six years experience in the characterization of SOI materials, including the effect of processing steps on the SOL (Silicon Over Layer) morphology, the residual stress in the SOL, buried oxide and handle wafer and, finally, the electrical properties. The effect of 3C-SiC deposition on SOI has also been considered.

Facilities and Equipment:

Numerous optical and electrical characterization techniques are available at G.E.S.

- Double X-ray Diffraction (DDX).
- Two different set-up to perform electrical (Hall effect and resistivity) measurements in the temperature range: 4 K – 300 K (with high hydrostatic pressure and/or high magnetic field) and 300K – 1000 K.
- Micro-Infrared and Micro-Raman set-up
- LTPL (Low Temperature Photo-Luminescence) set-up.

Three last international research projects:

- « SICOIN » (European Brite-Euram Contract, 1997-2000, BRPR-CT96-0261) : Pressure Sensor based on 3C-SiCon Si or SOI.
- « HERO » (EURISMUS, 1999-2003, HERO.n°EM.57) : Hall sensor based on SOI.